VS-25TTS08S-M3, VS-25TTS12S-M3 Series

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Thyristor, Surface Mount, Phase Control SCR, 16 A



PRIMARY CHARACTERISTICS							
I _{T(AV)}	16 A						
V _{DRM} /V _{RRM}	800 V, 1200 V						
V_{TM}	1.25 V						
I _{GT}	45 mA						
T _J	-40 to +125 °C						
Package	D ² PAK (TO-263AB)						
Circuit configuration	Single SCR						

FEATURES

 Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C



 Designed and qualified according JEDEC®-JESD 47

 Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

DESCRIPTION

The VS-25TTS...S-M3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS									
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS									
NEMA FR-4 or G10 glass fabric-based epoxy with 4 oz. (140 µm) copper	3.5	5.5							
Aluminum IMS, R _{thCA} = 15 °C/W	8.5	13.5	A						
Aluminum IMS with heatsink, R _{thCA} = 5 °C/W	16.5	25.0							

Note

• $T_A = 55$ °C, $T_J = 125$ °C, footprint 300 mm²

MAJOR RATINGS AND CHARACTERISTICS									
PARAMETER TEST CONDITIONS VALUES UNITS									
I _{T(AV)}	Sinusoidal waveform	16	۸						
I _{RMS}		25	А						
V _{RRM} /V _{DRM}		800 to 1200	V						
I _{TSM}		350	A						
V _T	16 A, T _J = 25 °C	1.25	V						
dV/dt		500	V/µs						
dl/dt		150	A/µs						
T _J		-40 to +125	°C						

VOLTAGE RATINGS									
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} , AT 125 °C mA						
VS-25TTS08S-M3	800	800	10						
VS-25TTS12S-M3	1200	1200]						



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ABSOLUTE MAXIMUM RATINGS									
DADAMETED	SYMBOL	TEC	VAL	LINUTO					
PARAMETER	STINIBUL	SYMBOL TEST CONDITIONS				UNITS			
Maximum average on-state current	I _{T(AV)}	T _C = 93 °C, 180° c	onduction half sine wave	16					
Maximum RMS on-state current	I _{RMS}			2	5	Α			
Maximum peak, one-cycle,	L	10 ms sine pulse,	rated V _{RRM} applied	30	00	A			
non-repetitive surge current	I _{TSM}	10 ms sine pulse,	no voltage reapplied	35	50				
Maximum I ² t for fusing	l ² t	10 ms sine pulse,	rated V _{RRM} applied	4	50	A ² s			
Maximum I-t for fusing	i-r	10 ms sine pulse,	630		A-8				
Maximum I ² √t for fusing	I ² √t	t = 0.1 ms to 10 m	6300		A²√s				
Maximum on-state voltage drop	V_{TM}	16 A, T _J = 25 °C		1.25		V			
On-state slope resistance	r_t $T_J = 125 ^{\circ}\text{C}$		2.0	mΩ					
Threshold voltage	V _{T(TO)}	$V_{T(TO)} \qquad \qquad \qquad \qquad \qquad \qquad \qquad \qquad \qquad \qquad $.0	V				
Maximum reverse and direct leakage current	l/l	T _J = 25 °C	V= = rated V== \/ =	0	.5				
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	T _J = 125 °C	$V_R = \text{rated } V_{RRM} / V_{DRM}$ 10		0				
Holding current	I _H	VS-25TTS08, VS-25TTS12	Anode supply = 6 V, resistive load, initial $I_T = 1$ A, $T_J = 25$ °C	-	150	mA			
Maximum latching current	ΙL	Anode supply = 6 V, resistive load, T _J = 25 °C			00				
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J$ max., linear to 80 %, $V_{DRM} = R_g - k = open$			00	V/µs			
Maximum rate of rise of turned-on current	dl/dt	-			150				

TRIGGERING									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Maximum peak gate power	P _{GM}		8.0	W					
Maximum average gate power	P _{G(AV)}		2.0	VV					
Maximum peak positive gate current	+ I _{GM}		1.5	Α					
Maximum peak negative gate voltage	- V _{GM}		10	V					
	I _{GT}	Anode supply = 6 V, resistive load, T _J = - 10 °C	60						
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, T _J = 25 °C	45	mA					
		Anode supply = 6 V, resistive load, T _J = 125 °C	20	ſ					
		Anode supply = 6 V, resistive load, T _J = - 10 °C	2.5						
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	2.0						
		Anode supply = 6 V, resistive load, T _J = 125 °C	1.0	V					
Maximum DC gate voltage not to trigger	V_{GD}	T 105 °C V reted value	0.25	1					
Maximum DC gate current not to trigger	I_{GD}	T _J = 125 °C, V _{DRM} = rated value	2.0	mA					

SWITCHING									
PARAMETER SYMBOL TEST CONDITIONS VALUES UNIT									
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9						
Typical reverse recovery time	t _{rr}	T. _I = 125 °C	4	μs					
Typical turn-off time	tq	1j = 125 C	110	1					



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THERMAL AND MECHANICAL SPECIFICATIONS									
PARAMETER	PARAMETER SYMBOL TEST CONDITIONS VA								
Maximum junction and storage temperature range	T _J , T _{Stg}		-40 to +125	°C					
Maximum thermal resistance, junction to case		DC operation	1.1	°C/W					
Typical thermal resistance, junction to ambient (PCB mount)	R _{thJA} ⁽¹⁾		40	C/VV					
Approximate weight			2	g					
Approximate weight			0.07	OZ.					
Marking device		Case style D ² PAK (TO-263AB)	25TTS08S						
ivial killy device		Case style D-FAR (10-203AB)	25TTS12S						

Note

⁽¹⁾ When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 µm] copper 40 °C/W. For recommended footprint and soldering techniques refer to application note #AN-994

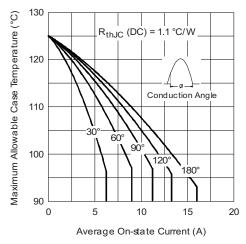


Fig. 1 - Current Rating Characteristics

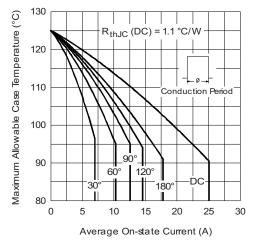


Fig. 2 - Current Rating Characteristics

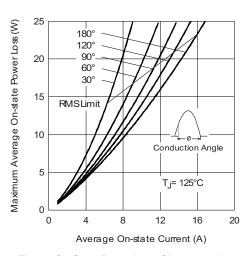


Fig. 3 - On-State Power Loss Characteristics

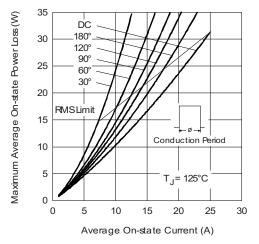


Fig. 4 - On-State Power Loss Characteristics



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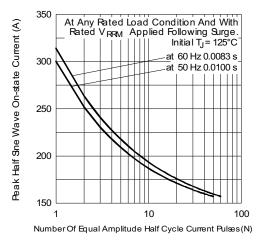


Fig. 5 - Maximum Non-Repetitive Surge Current

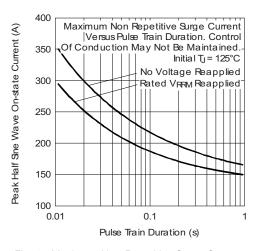


Fig. 6 - Maximum Non-Repetitive Surge Current

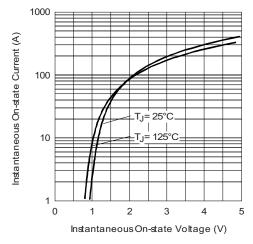
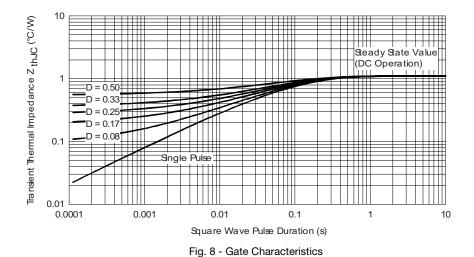


Fig. 7 - On-State Voltage Drop Characteristics



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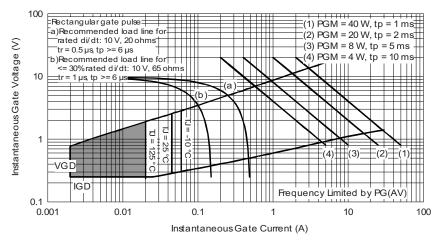
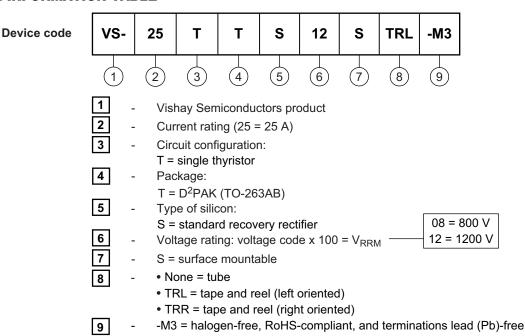


Fig. 9 - Thermal Impedance Z_{thJC} Characteristics

ORDERING INFORMATION TABLE



ORDERING INFORMATION (Example)									
PREFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPT									
VS-25TTS08S-M3	50	1000	Antistatic plastic tubes						
VS-25TTS08STRR-M3	800	800	13" diameter reel						
VS-25TTS08STRL-M3	800	800	13" diameter reel						
VS-25TTS12S-M3	50	1000	Antistatic plastic tubes						
VS-25TTS12STRR-M3	800	800	13" diameter reel						
VS-25TTS12STRL-M3	800	800	13" diameter reel						

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?96164					
Part marking information	www.vishay.com/doc?95444					
Packaging information	www.vishay.com/doc?96424					

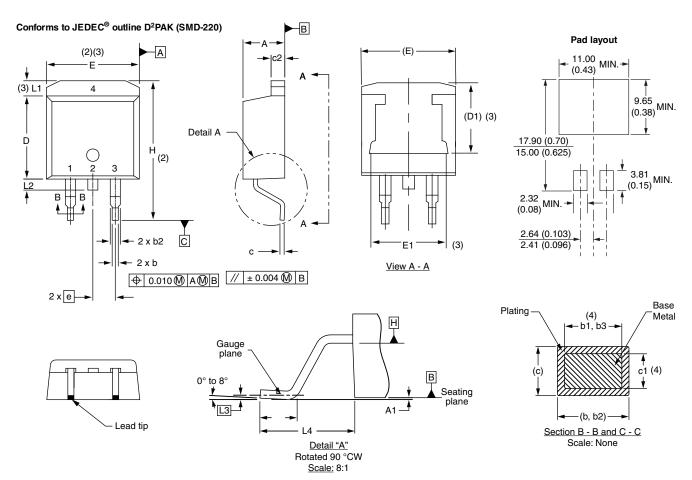
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D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES	NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

Revision: 13-Jul-17 Document Number: 96164

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